



NTH4L060N090SC1

Silicon Carbide MOSFET, N-Channel, 900 V, 60 mΩ, TO247-4L

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

- High Junction Temperature
- 900V Rating
- 100% UIL Tested
- RoHS Compliant
- 175°C
- DC-DC Converter
- Boost Inverter
- UPS
- Solar
- Power Devices

	Pricing (\$/Unit)	Compliance	Status	Family	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on) Typ @ 25°C} (mΩ)	Q _g Total (nC)	Output Capacitance (pF)	T _J Max (°C)	Package Type
NTH4L060N090SC1	6.2792	 	Active	M2	900	67	60	61.8	107	175	TO-247-4